



# Transparent conductive oxides for silicon heterojunction solar cells

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FROM RESEARCH TO INDUSTRY  
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 **ines**  
INSTITUT NATIONAL  
DE L'ENERGIE SOLAIRE

Introduction: presentation of the National Institute for Solar Energy (INES)

Silicon heterojunction (SHJ) solar cells

- Structure and operation
- Role of TCOs in SHJ cells
- SHJ solar cells and modules at INES

TCOs for SHJ cells

- Baseline TCO at INES
- Alternative TCO options
- Example of alternative TCO options tested at INES

Conclusions

**Covering the whole value chain, from material to systems including building integration and solar mobility**

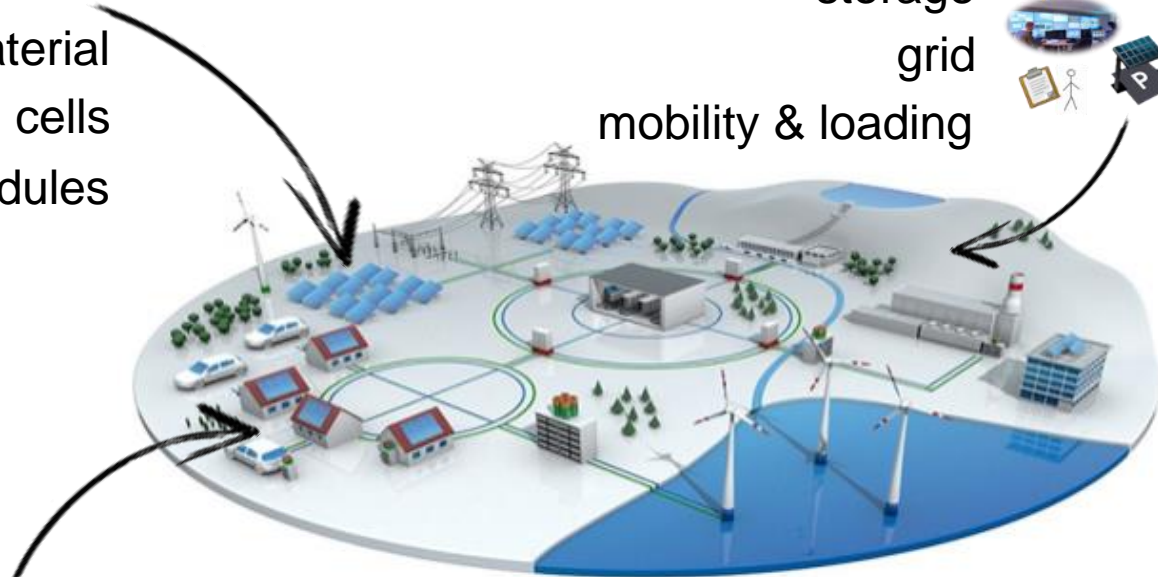
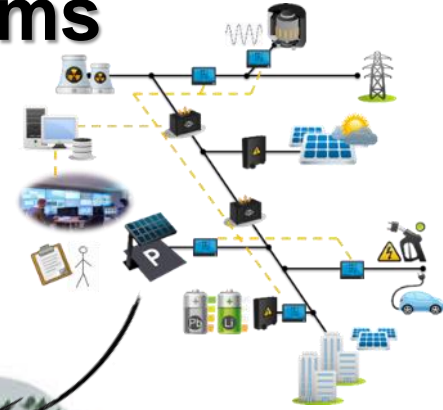
## photovoltaic



material  
 cells  
 modules

## systems

software & electronics  
 storage  
 grid  
 mobility & loading



## building

Thermal systems  
 envelope  
 management



~ 450-500 persons



200 industrial partners



~ 70 patents a year



Budget ~ 60 M€

Introduction: presentation of the National Institute for Solar Energy (INES)

## **Silicon heterojunction (SHJ) solar cells**

- **Structure and operation**
- **Role of TCOs in SHJ cells**
- **SHJ solar cells and modules at INES**

## TCOs for SHJ cells

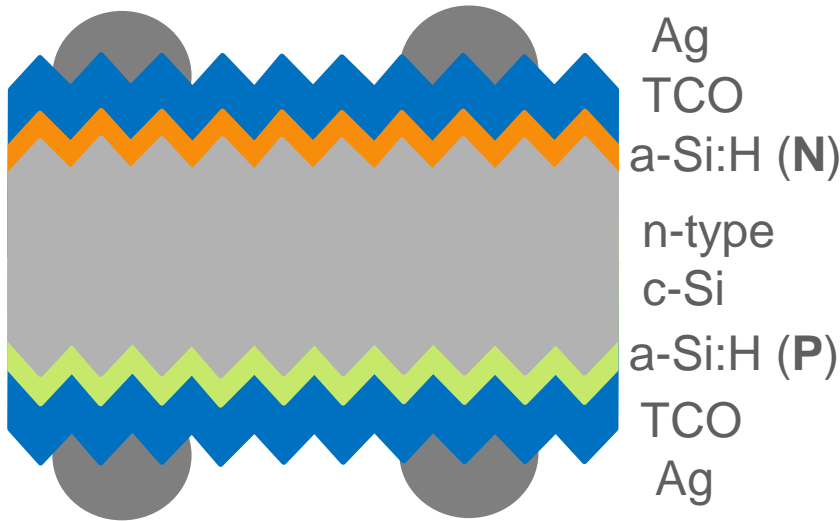
- Baseline TCO at INES
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## Conclusions

# SILICON HETEROJUNCTION (SHJ) SOLAR CELLS

## Structure and operation

### a-Si:H/c-Si heterojunction solar cell



- High  $\eta$  (25.1% [1], 26.7% IBC [2]) thanks to very high  $V_{OC}$
- Bifacial device
- Low temperature (< 200°C) processes
- Simple process
- Compatible with thin wafers

**BUT:**

1. Very low conductivity of a-Si:H (<10<sup>-2</sup> S/cm)  
→ Lateral conduction is not enough for carrier collection (↓ FF)
2. a-Si:H does not have antireflecting properties (↓  $J_{SC}$ )



**Need  
of TCOs!**

[1] D. Adachi et al., Applied Physics Letters, 107, 233506 (2015)

[2] K. Yoshikawa et al, Nat Energy. 2, 17032 (2017)

### Electrical requirements

1. **Carrier transport** to the metal contacts at the front and back side
2. **Low contact resistivity** with metal contacts and with a-Si:H layers

### Optical requirements

1. **Antireflection** coating
2. **Transparence** 300-1200 nm, limited IR absorption

### No degradation of the a-Si:H layers

1. **Soft deposition** conditions ( $T < 200^{\circ}\text{C}$ , low ion bombardment...)
2. **Diffusion barrier** to metallic impurities (Cu...)

### Adapted for module integration

1. **Stability** in time, no reaction with encapsulation material
2. **No ageing** with air/water...

# SILICON HETEROJUNCTION (SHJ) SOLAR CELLS

## SHJ solar cells and modules at INES

### Pre-industrial production line for silicon heterojunction solar cells

- <10h from wafer to cell
- Up to 2400 wafers/hour

➔ R&D with statistics

### Numerous industrial and institutional partners

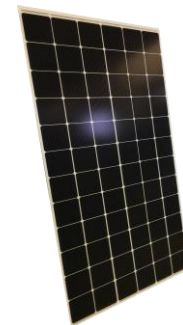


➔ Versatile research



| Configuration     | Record $\eta$ |
|-------------------|---------------|
| 4 busbars (BB4)   | 22.8%         |
| 5 busbars (BB5)   | 23.1%         |
| 6 busbars (BB6)   | 23.1%         |
| Busbar-less (BB0) | 23.5%         |

410 W<sub>P</sub>  
72-cell  
module



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**TCOs for SHJ cells**

- **Baseline TCO at INES**
- **Alternative TCO options**
- **Example of alternative TCO options tested at INES**

Conclusions



### Sputtered $\text{In}_2\text{O}_3:\text{Sn}$ (ITO)

- Industrial in-line sputtering tool by Meyer Burger: up to 2400 w/h
- $\text{In}_2\text{O}_3/\text{SnO}_2$  3 wt% rotary targets
- Simultaneous front and back side deposition

### Limitations of sputtered ITO

1. Limited mobility
  - $\sigma/T$  compromise  $\rightarrow$  FF/ $J_{\text{SC}}$  compromise
  - $\sigma = qN\mu$
  - But: high N generates free carrier absorption (FCA)
    - ➔ need of **high  $\mu$  material**
2. High ion bombardment induced by sputtering
  - Degradation of a-Si:H layers  $\rightarrow$   $V_{\text{OC}}$  and FF  $\downarrow$ 
    - ➔ need of **soft deposition techniques**
3. Scarcity and costliness of In
  - ➔ need of **In-free TCOs** to  $\downarrow$  costs

# TCOS FOR SHJ SOLAR CELLS










## Alternative TCO options

|                                   | PVD        |      | CVD   |     |         |
|-----------------------------------|------------|------|-------|-----|---------|
|                                   | Sputtering | RPD  | MOCVD | ALD | AP-SALD |
| ITO:H                             |            |      |       |     |         |
| In <sub>2</sub> O <sub>3</sub> :H |            |      |       |     |         |
| In <sub>2</sub> O <sub>3</sub> :W |            | <br> |       |     |         |
| ZnO:Al                            |            |      |       |     |         |
| ZnO:B                             |            |      |       |     |         |

High-μ TCO
 Low-damage
 In-free TCO

# TCOS FOR SHJ SOLAR CELLS

Alternative TCO options tested on INES SHJ cells

|                                   | Sputtering  | RPD   | MOCVD   | ALD   | AP-SALD   |
|-----------------------------------|---|---|---|---|---|
| ITO:H                             |  |   |   |   |   |
| In <sub>2</sub> O <sub>3</sub> :H |  |   |   |  |   |
| In <sub>2</sub> O <sub>3</sub> :W |  |  |   |   |   |
| ZnO:Al                            |  |   |   |  |  |
| ZnO:B                             |   |   |  |   |   |



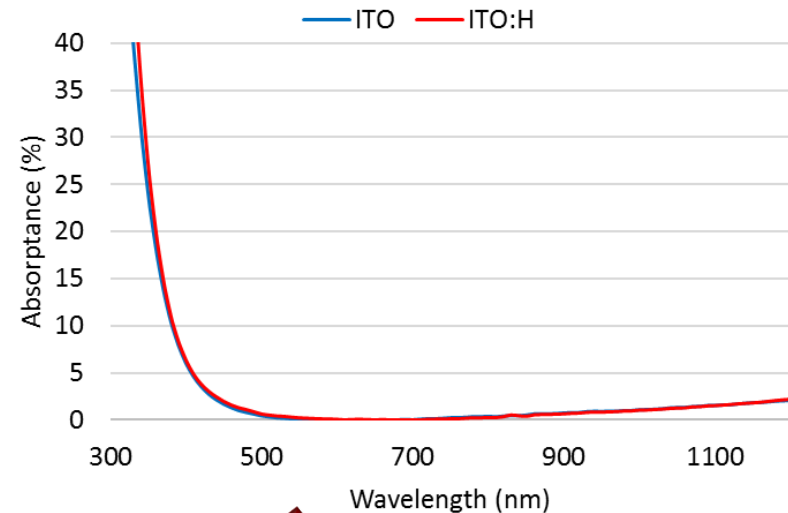
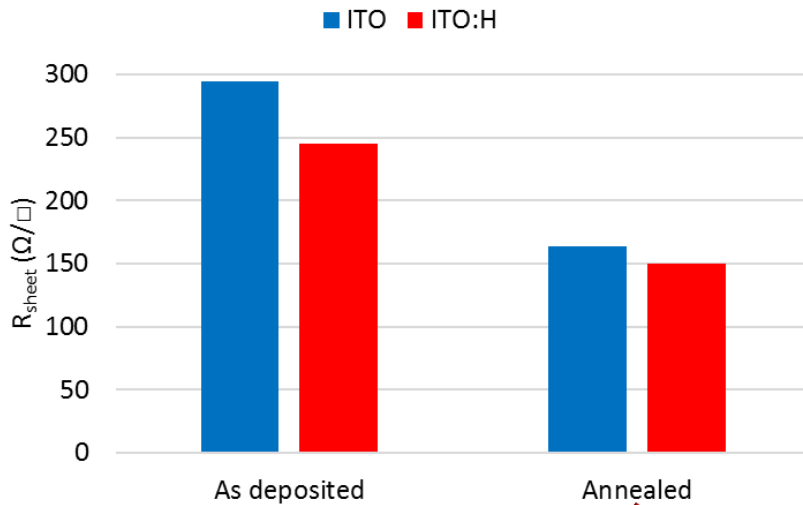
Tested on SHJ cells produced at INES



Presented here

### ITO:H:

- Slightly less resistive than ITO
- Similar absorptance as ITO, including in the near-IR



Bifacial  
BB0 cell  
results

|       | Voc<br>(mV) | FF<br>(%)    | Jsc<br>(mA/cm <sup>2</sup> ) | $\eta$<br>(%) |
|-------|-------------|--------------|------------------------------|---------------|
| ITO   | 731.1       | 79.99        | 37.93                        | 22.16         |
| ITO:H | 731.2       | <b>80.59</b> | 37.90                        | <b>22.31</b>  |

# TCOS FOR SHJ SOLAR CELLS

## Alternative TCO options: sputtered $\text{In}_2\text{O}_3:\text{H}$ (IOH)

### IOH

- Very low  $R_{\text{sheet}}$  thanks to very high  $\mu$
- Very low absorption thanks to limited N

| $R_{\text{sheet}}$<br>( $\Omega/\square$ ) | N<br>( $\text{cm}^{-3}$ ) | $\mu$<br>( $\text{cm}^2/\text{V/s}$ ) | $A_{300-1200\text{nm}}$<br>(%) |
|--|---------------------------|---------------------------------------|--------------------------------|
| 30   | 1.4E20                    | 140                                   | 1.1                            |

### Electroplated BB4 cell results

| Front/back<br>contact | $V_{\text{oc}}$<br>(mV) | $J_{\text{sc}}$<br>( $\text{mA}/\text{cm}^2$ ) | FF<br>(%) | $\eta$<br>(%) |
|-----------------------|-------------------------|--|-----------|---------------|
| ITO/ITO               | 723.8                   | 36.8   | 80.3      | 21.4          |
| ITO/IOH               | 728.9                   | 37.4   | 79.2      | 21.6          |
| IOH/IOH               | 728.3                   | 37.5   | 79.4      | 21.7          |

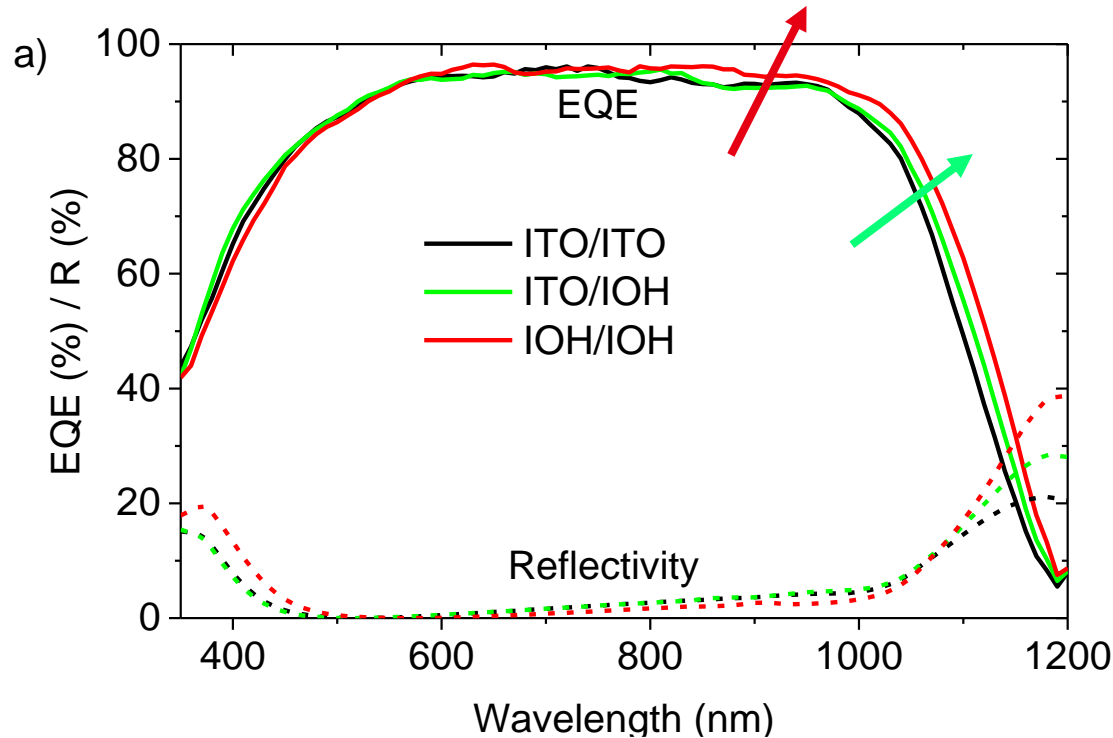


$\eta$   $\uparrow$  with IOH thanks to significant  $J_{\text{sc}}$   $\uparrow$  and despite FF  $\downarrow$  due to worse electrical contact

# TCOS FOR SHJ SOLAR CELLS

Alternative TCO options: sputtered  $\text{In}_2\text{O}_3:\text{H}$  (IOH)

## IOH: where is the current gain?



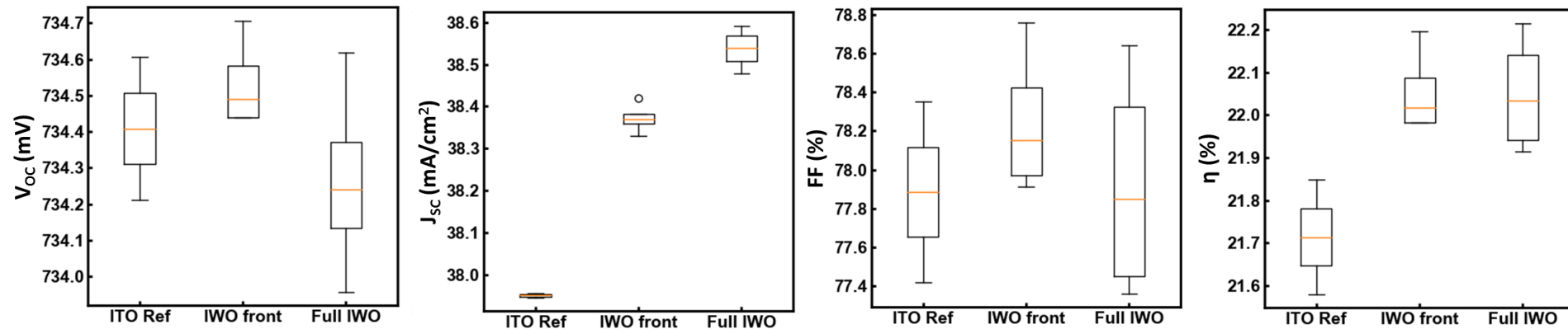
↑ **EQE in the near-IR range when replacing ITO by IOH**  
 → low N of IOH layers leading to lower FCA in the near-IR

# TCOS FOR SHJ SOLAR CELLS

Alternative TCO options: sputtered  $\text{In}_2\text{O}_3:\text{W}$  (IWO)

## IWO

- High- $\mu$  TCO:  $> 80 \text{ cm}^2/\text{V}/\text{s}$
- Developed by CSEM (Swiss Center for Electronics and Microtechnique) and integrated on INES SHJ cells in the framework of EU project AMPERE



G. Christmann et al., 35th EUPVSEC proceedings, to be published (2018)

Strong  $J_{sc} \uparrow$  with IWO as front TCO, even higher  $J_{sc}$  with double-side IWO application

Similar FF as ITO



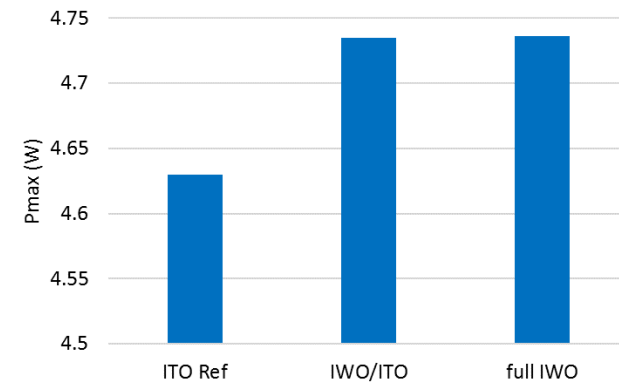
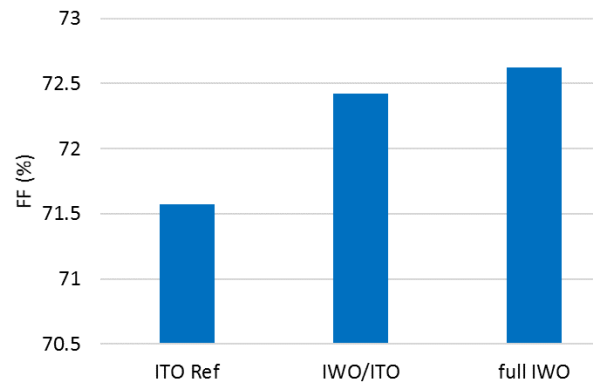
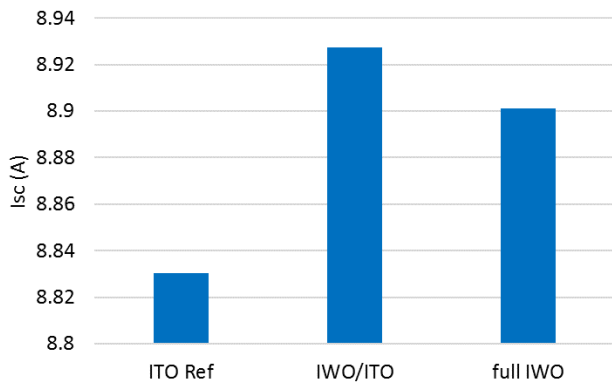
Significant efficiency gain with IWO compared to ITO

# TCOS FOR SHJ SOLAR CELLS

## Alternative TCO options: sputtered $\text{In}_2\text{O}_3:\text{W}$ (IWO)

### IWO: gain confirmed in module

- 1-cell mini-modules for this 1st test
- 2 modules/condition



Potential: +7-8 W in a 72-cell module



# TCOS FOR SHJ SOLAR CELLS


## Alternative TCO options: sputtered ZnO:Al (AZO)

In collaboration with  MEYER BURGER

### AZO

- Cheap In-free material
- High  $R_{sheet}$  due to low  $\mu$
- Slightly higher absorption than ITO

Slightly lower  $J_{sc}$  with AZO  
FF  $\downarrow\downarrow$  with AZO, especially when integrated at the back

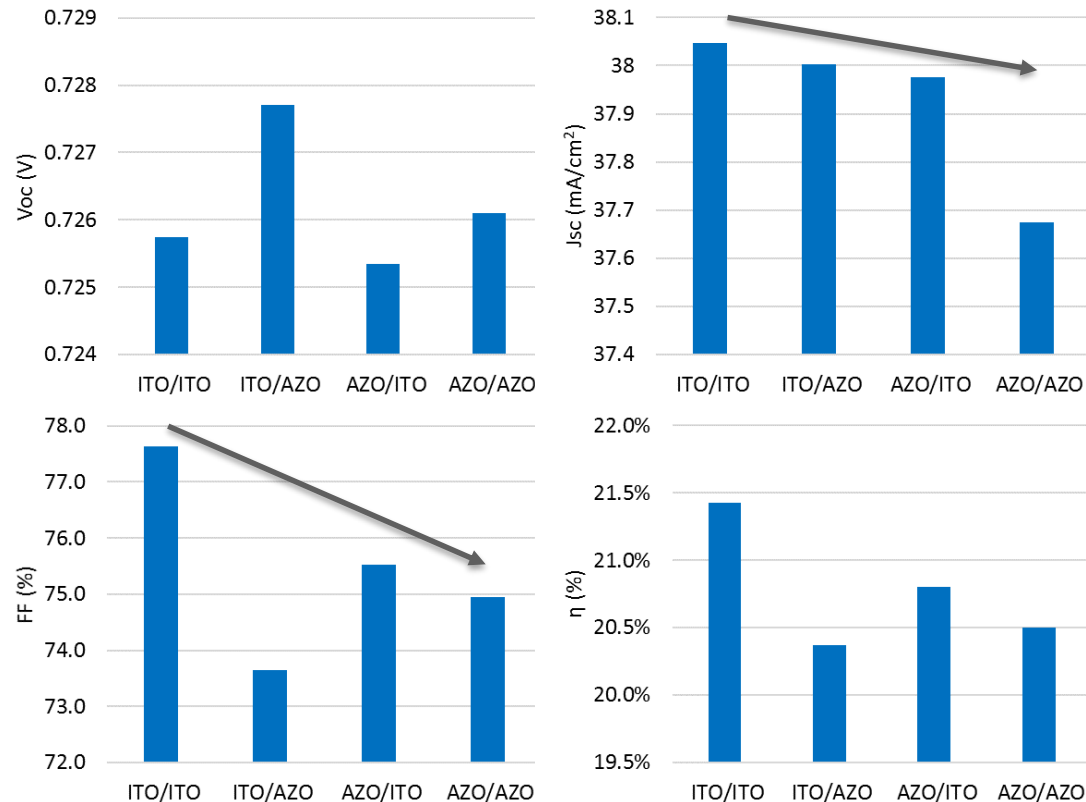
  $\eta \downarrow$  with AZO

But: **acceptable performance with front AZO** only

**What about stability?**

| $R_{sheet}$<br>( $\Omega/\square$ ) | N<br>( $cm^{-3}$ ) | $\mu$<br>( $cm^2/V/s$ ) | $A_{300-1200nm}$<br>(%) |
|-------------------------------------|--------------------|-------------------------|-------------------------|
| 200-300                             | 2.5-3E20           | 7-14                    | 3                       |

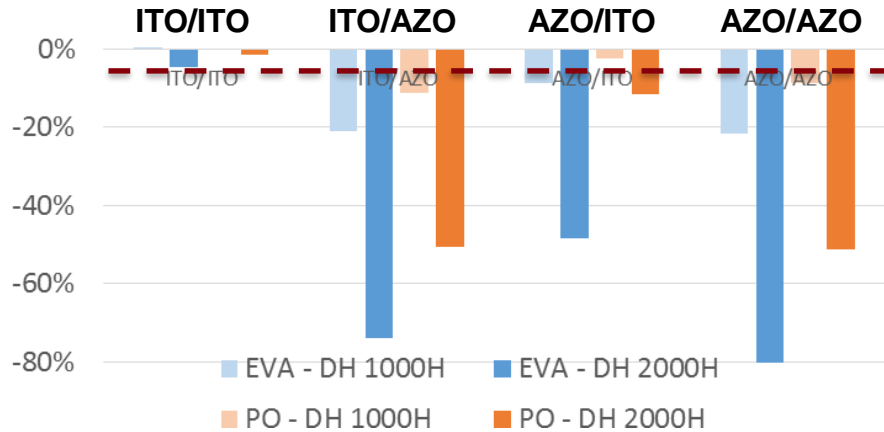
### Bifacial BB0 cell results



### AZO: module reliability

- 4-cell mini-modules
- 4 TCO configurations: ITO/ITO, ITO/AZO, AZO/ITO, AZO/AZO
- 2 different encapsulations: polyolefin (PO) vs ethylene-vinyl acetate (EVA)
- module degradation after 1000h and 2000h damp-heat test (85°C, 85% humidity)

#### Front/Back TCO



IEC-61215 norm: <5% degradation after 1000h of DH

Good reliability of the ITO/ITO modules regardless of encapsulation material  
 AZO/ITO + PO: OK after 1000h of DH  
 But: after 2000h of DH, bad reliability of all modules containing AZO

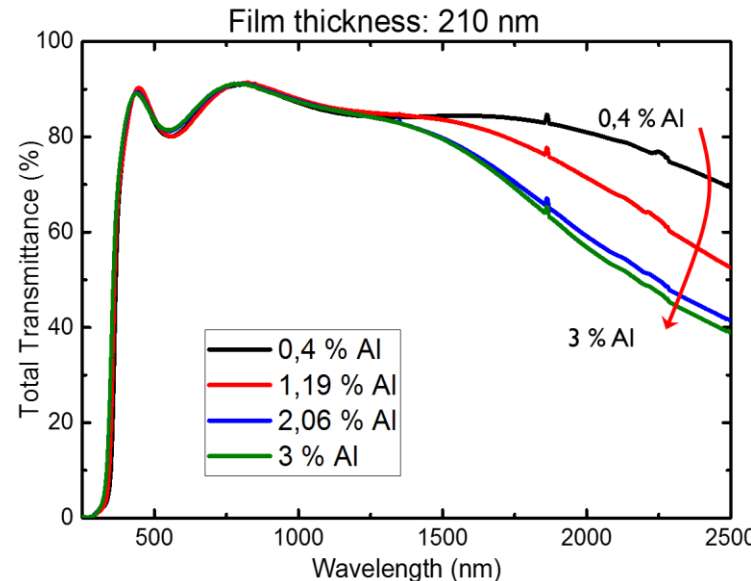
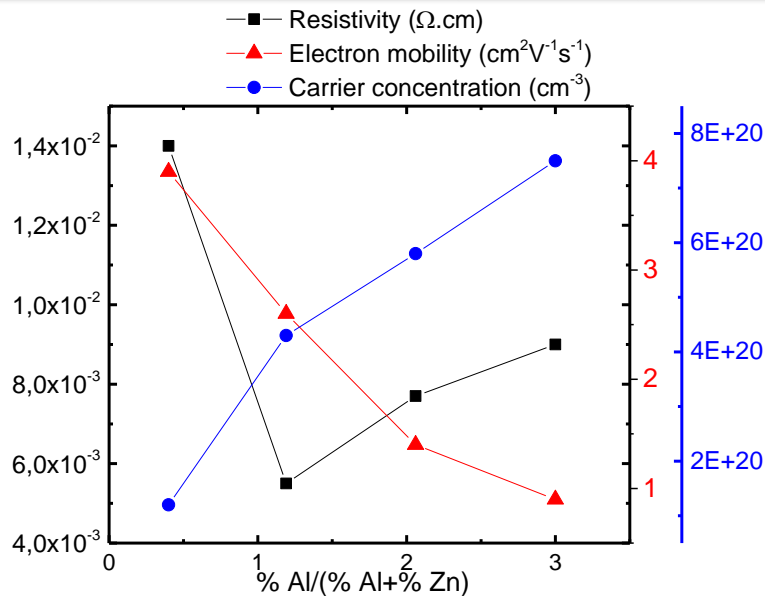
### AP-SALD AZO

Developped by LMGP (Materials and Physical Engineering Laboratory) in the framework of ANR DESPATCH project



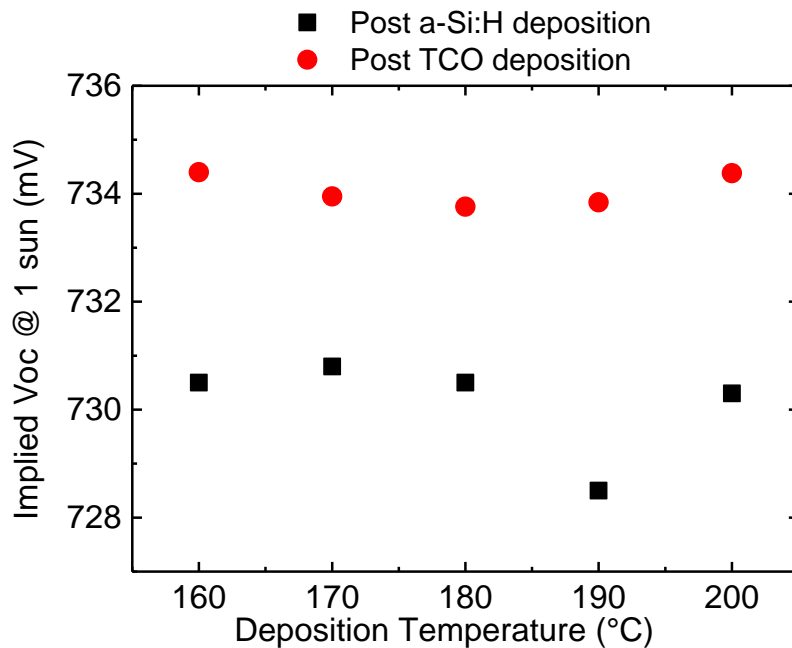
- Cheap In-free material
- Low-damage deposition method
- Fast and easily scalable deposition method
- High  $R_{\text{sheet}}$  due to very low  $\mu$
- High transmission in the 300-1200 nm range

Learn more on SALD AZO:  
V. Nguyen, TCM030,  
Wednesday 17<sup>th</sup> at 17:40

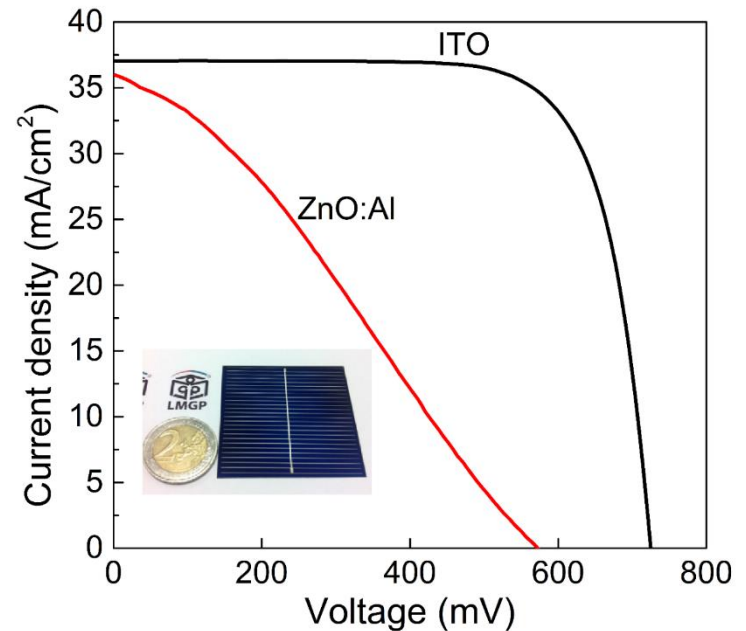


### AP-SALD AZO: application on CEA-INES SHJ solar cells

Quasi-steady-state photoconductance measurement



Light I(V) measurement



$i$ - $V_{OC}$  slightly  $\uparrow$  after AZO deposition



No degradation of the passivation with SALD AZO

But: very poor cell performance due high series resistance

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**Conclusions**

|                   | Sputtering | RPD  | MOCVD | ALD  | AP-SALD |
|-------------------|------------|------|-------|------|---------|
| ITO / ITO:H       | <br>       | <br> |       |      |         |
| New In-based TCOs | <br>       | <br> |       | <br> | <br>    |
| In-free TCOs      | <br>       |      | <br>  | <br> | <br>    |

Mobility 
 Bombardment 
 Reliability 
 Cost 
 Compatibility with mass production



Best alternative to sputtered ITO: new In-based TCOs by RPD

**Thank you for your  
attention!**



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**cea tech**



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ANR DESPATCH project (special thanks to V. Nguyen)